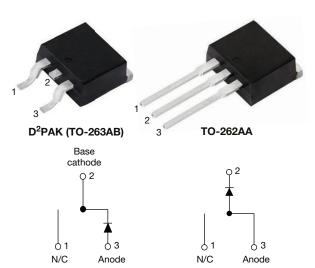
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# VS-8ETU04S-M3, VS-8ETU04-1-M3

Vishay Semiconductors

# Ultrafast Rectifier, 8 A FRED Pt<sup>®</sup>



VS-8ETU04S-M3

VS-8ETU04-1-M3

PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	8 A				
V <sub>R</sub>	400 V				
V <sub>F</sub> at I <sub>F</sub>	0.94 V				
t <sub>rr</sub> typ.	35 ns				
T <sub>J</sub> max.	175 °C				
Package	D <sup>2</sup> PAK (TO-263AB), TO-262AA				
Circuit configuration	Single				

## FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

## **DESCRIPTION / APPLICATIONS**

Vishay Semiconductors FRED Pt<sup>®</sup> series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Repetitive peak reverse voltage	V <sub>RRM</sub>		400	V
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 155 °C	8	
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	100	А
Repetitive peak forward current	I <sub>FRM</sub>		16	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C

ELECTRICAL SPECIFIC	ELECTRICAL SPECIFICATIONS (T <sub>J</sub> = 25 °C unless otherwise specified)					
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	400	-	-	
Forward voltage	VF	I <sub>F</sub> = 8 A	-	1.19	1.3	V
Forward voltage	۷F	I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	0.94	1.0	
Reverse leakage current		$V_{R} = V_{R}$ rated	-	0.2	10	
neverse leakage current	I <sub>R</sub>	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	20	500	μA
Junction capacitance	CT	V <sub>R</sub> = 400 V	-	14	-	pF
Series inductance	LS	Measured lead to lead 5 mm from package body	-	8.0	-	nH

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DYNAMIC RECOVERY CHARA	CTERISTIC	<b>CS</b> (T <sub>J</sub> = 25 °C u	nless otherwise s	pecified	)		
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	= 50 A/µs, V <sub>R</sub> = 30 V	-	35	60	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	$I_F = 8 A$	-	43	-	ns
		T <sub>J</sub> = 125 °C		-	67	-	
Poole recovery ourrept		T <sub>J</sub> = 25 °C		-	2.8	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 200 A/µs V <sub>B</sub> = 200 V	-	6.3	-	A
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C	VR - 200 V	-	60	-	nC
neverse recovery charge	Qrr	T <sub>J</sub> = 125 °C		-	210	-	10

THERMAL - MECHANICAL SP	ECIFICATI	ONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	1.8	2.0	
Thermal resistance, junction-to-ambient	R <sub>thJA</sub>	Typical socket mount	-	-	50	°C/W
Thermal resistance, case-to-heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.5	-	0,11
Waight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking davias		Case style D <sup>2</sup> PAK (TO-263AB)		8ETU	J04S	•
Marking device		Case style TO-262AA		8ETL	J04-1	

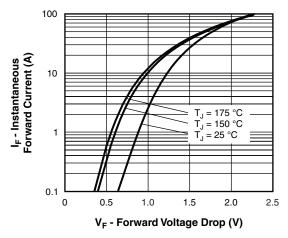


Fig. 1 - Typical Forward Voltage Drop Characteristics

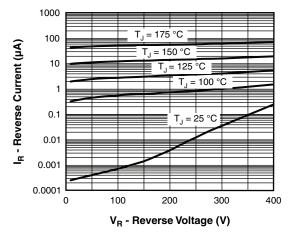


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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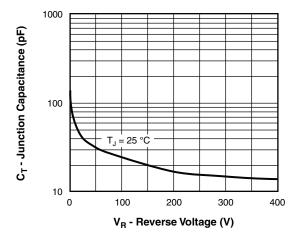


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

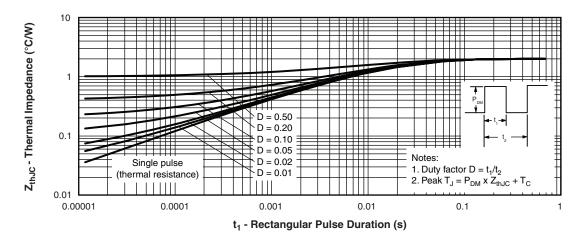
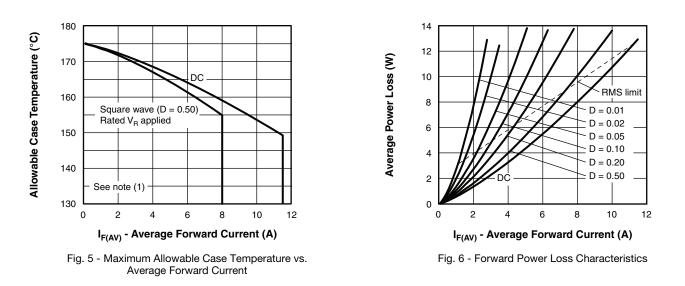


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics



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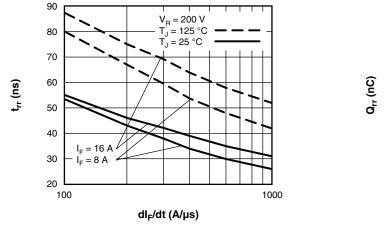


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

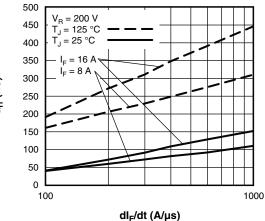


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;  $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

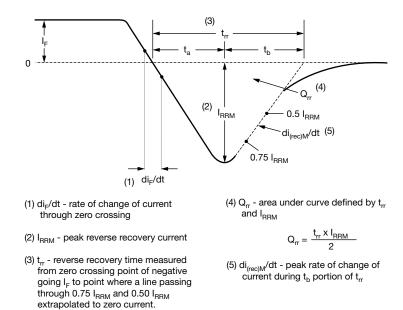


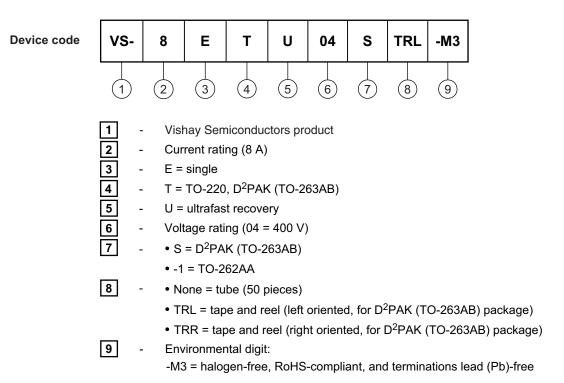
Fig. 9 - Reverse Recovery Waveform and Definitions

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## **ORDERING INFORMATION TABLE**

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ORDERING INFORMATION (Example)					
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION			
VS-8ETU04S-M3	50	Antistatic plastic tubes			
VS-8ETU04STRL-M3	800	13" diameter plastic tape and reel			
VS-8ETU04STRR-M3	800	13" diameter plastic tape and reel			
VS-8ETU04-1-M3	50	Antistatic plastic tubes			

LINKS TO RELATED DOCUMEN	TS	
Dimensions -	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96164
Dimensions	TO-262AA	www.vishay.com/doc?96165
Part marking information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?95444
Fart marking information	TO-262AA	www.vishay.com/doc?95443
Packaging information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96424

**Vishay Semiconductors** 

D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIMETERS		INC	NOTES	
STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	2.54 BSC		0.100 BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	0.010	BSC	
L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

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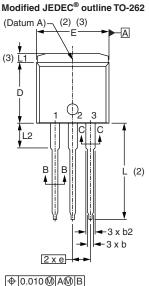
## **Outline Dimensions**

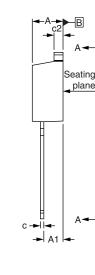


**Vishay Semiconductors** 

**TO-262AA** 

#### **DIMENSIONS** in millimeters and inches





F D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None





Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode

Lead assignments

CYMPOL	MILLIN	IETERS	INC	HES	NOTES
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100	) BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

 <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second dimensioner of the second dimensis of the second dimensioner of the second dimensioner of the the outmost extremes of the plastic body (3)

Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only (5)

Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

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